

NPN resistor-equipped transistor; $R1 = 22 \text{ k}\Omega$, $R2 = 22 \text{ k}\Omega$ Rev. 1 — 16 May 2012Product data of the second seco

Product data sheet

Product profile 1.

1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA124EMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 gualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



NPN resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		3
3	0	output (collector)	2 Transparent top view SOT883B (DFN1006B-3)	1 R2 2 sym007

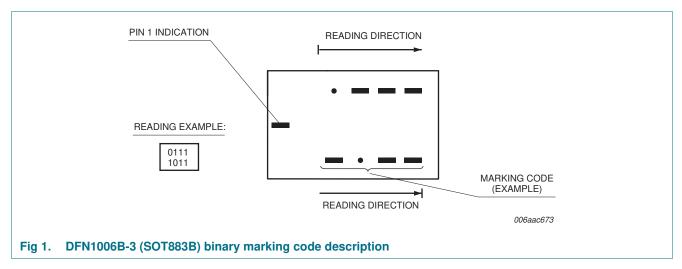
3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PDTC124EMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

4. Marking

Table 4.	Marking	codes
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Type number	Marking code
PDTC124EMB	0011 0111



NPN resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

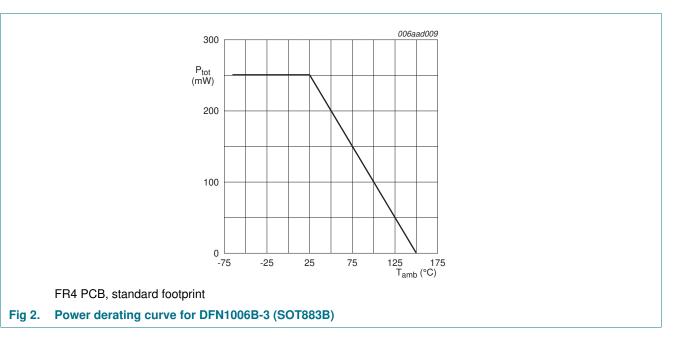
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		, , , , ,				
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	10	V
VI	input voltage	positive		-	40	V
		negative		-	-10	V
lo	output current			-	100	mA
I _{CM}	peak collector current	pulsed; t _p ≤ 1 ms		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

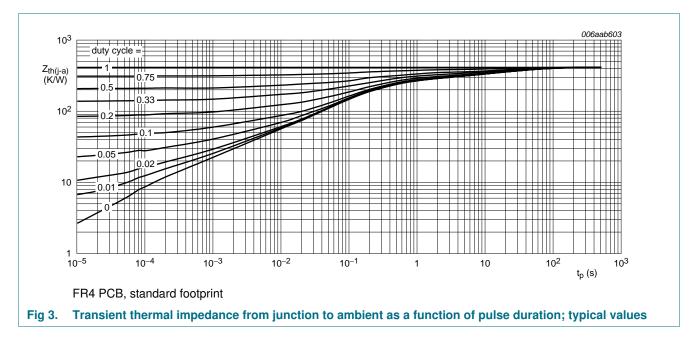


NPN resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

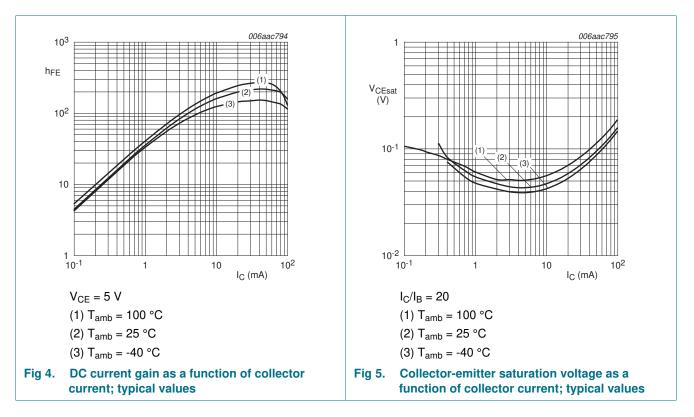


NPN resistor-equipped transistor; R1 = 22 k Ω , R2 = 22 k Ω

7. Characteristics

Table 7.	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE}=30~V;~I_B=0~A;~T_{amb}=25~^\circ C$		-	-	100	nA
	current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 \text{ °C}$		-	-	5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$		-	-	180	μA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 5 mA; T_{amb} = 25 °C		60	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
V _{I(off)}	off-state input voltage	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 100 \mu\text{A}; \text{ T}_{amb} = 25 ^{\circ}\text{C}$		-	1.1	0.8	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; \text{ I}_{C} = 5 \text{ mA}; \text{ T}_{amb} = 25 \text{ °C}$		2.5	1.7	-	V
R1	bias resistor 1 (input)	T _{amb} = 25 °C		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C _C	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	2.5	pF
f _T	transition frequency	V_{CE} = 5 V; I _C = 10 mA; f = 100 MHz; T _{amb} = 25 °C	[1]	-	230	-	MHz
							-

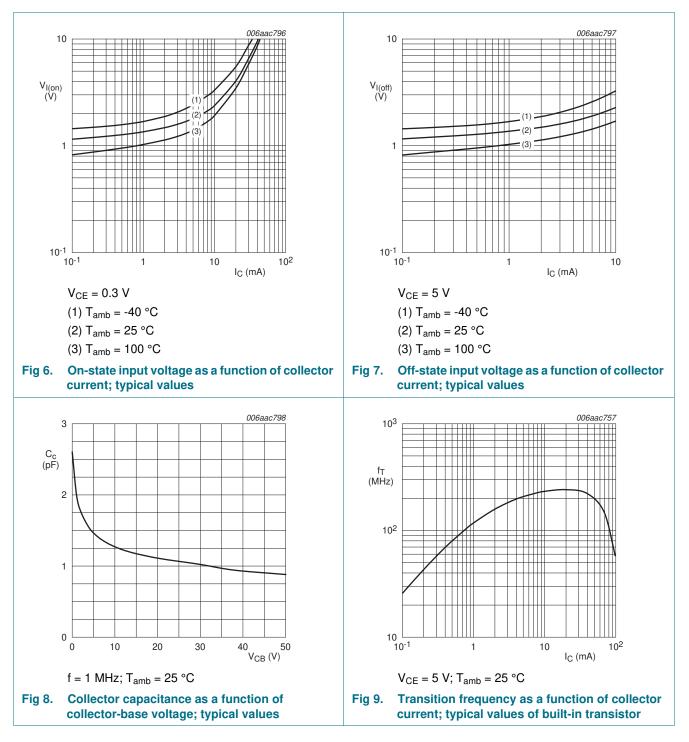
[1] Characteristics of built-in transistor.



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8. Test information

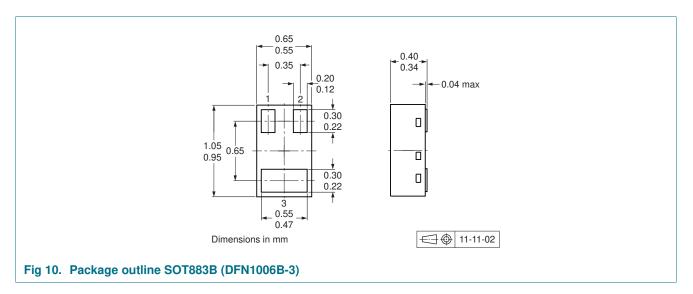
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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Package outline 9.



10. Soldering

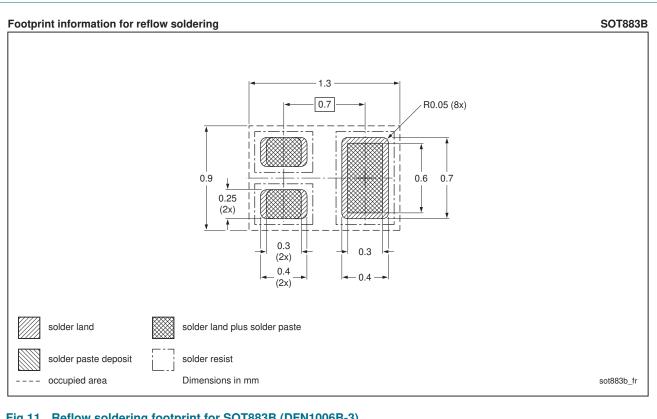


Fig 11. Reflow soldering footprint for SOT883B (DFN1006B-3)

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11. Revision history

Table 8. Revision h	. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTC124EMB v.1	20120516	Product data sheet	-	-			

12. Legal information

12.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions'

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